Si4701BDY vs. Si4701DY

Description: Load Switch with Level-Shift
Package: SO-8
Pin Out: Identical

Part Number Replacements:
Si4701BDY-T1-E3 Replaces Si4701DY-T1-E3
Si4701BDY-T1-E3 Replaces Si4701DY-T1

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Si4701BDY**	**Si4701DY**	**Unit**
Input Voltage		V_{IN}	30	30	V
ON/OFF Voltage		$V_{ON/OFF}$	8	8	
Load Current	Continuous	I_L	7.0	7.0	A
	Pulsed		± 30	± 30	
Continuous Intrinsic Diode Conduction		I_S	- 1.15	- 1.15	
Power Dissipation		P_D	1.25	1.25	W
Operating Junction and Storage Temperature Range		T_j and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	100	100	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
Parameter		**Symbol**	**Si4701BDY**			**Si4701DY**			**Unit**
			Min	**Typ**	**Max**	**Min**	**Typ**	**Max**	
OFF Characteristic									
Reverse Leakage Current		I_{FL}			1			1	µA
Diode Forward Voltage		V_{SD}		0.7	1		0.7	1	V
Dynamic									
On-Resistance (Q2)	V_{HV} = 10 V	$r_{DS(on)}$		0.012	0.015		0.012	0.015	Ω
	V_{HV} = 4.5 V			0.017	0.021		0.017	0.021	
On-State (Q2) Drain-Current	V_{HV} = 10 V	$I_{D(on)}$	20			20			A

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.